

IN THE CLAIMS

1 (Previously Presented). A method comprising:
optically programming a phase change memory after electrically programming said memory.

2 (Original). The method of claim 1 including forming a phase change memory with a pair of parallel spaced electrodes and a phase change material between said electrodes.

3 (Original). The method of claim 2 including arranging said phase change material and said electrodes laterally.

4 (Original). The method of claim 3 including enabling light exposure of said phase change material.

5 (Original). The method of claim 4 including enabling light exposure through a thermally insulating material.

6 (Original). The method of claim 3 including enabling said phase change material to be electrically accessed through rows and columns.

7 (Original). The method of claim 6 including locating said rows and columns to enable light access to said cells.

8 (Original). The method of claim 7 including positioning one of said rows and columns below said phase change material.

9 (Original). The method of claim 8 including providing a via coupling one of said electrodes to said underlying row or column.

10 (Previously Presented). The method of claim 1 including using the phase change memory to convert an optical signal to an electrical signal.

Claims 11-36 (Canceled).